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COMPLIANT

N-Channel 45 V (D-S) Power MOSFET

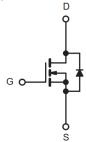
PRODUCT SUMMARY						
V _{DS} (V)	R _{DS(on)} (mΩ) (TYP.)	I _D (A) ^a	Q _g (TYP.)			
45	1.6 at V _{GS} = 10 V	180	59 nC			

FEATURES

- DT-Trench Power MOSFET
- 100 % Rg and UIS Tested
- Low RDS(ON)

APPLICATIONS

- Networking
- Load Switch



N-Channel MOSFET

TO-220 Pin Configuration



ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	LIMIT	UNIT				
Drain-Source Voltage	V _{DS}	45	V				
Gate-Source Voltage	V _{GS}	± 20	v				
Continuous Drain Current /T 150 °C	T _C = 25 °C	,	180				
Continuous Drain Current (T _J = 150 °C)	T _C = 70 °C	I _D	156				
Pulsed Drain Current	I _{DM}	720	A				
Avalanche Current L = 0.1 mH		I _{AS}	172				
Single Avalanche Energy ^a	L = U. I MH	E _{AS}	590	mJ			
Maximum Bower Dissipation 8	T _C = 25 °C	В	258 b	w			
Maximum Power Dissipation ^a	T _C = 70 °C	P _D	165 b				
Operating Junction and Storage Temperature Ra	T _J , T _{sta}	-55 to +150	°C				

THERMAL RESISTANCE RATINGS						
PARAMETER	SYMBOL	LIMIT	UNIT			
Junction-to-Ambient (PCB Mount) ^c	R_{thJA}	20	°C/W			
Junction-to-Case (Drain)	R _{thJC}	0.5	C/VV			

Notes

- a. Duty cycle \leq 1 %.
- b. See SOA curve for voltage derating.
- c. When mounted on 1" square PCB (FR4 material).



SPECIFICATIONS (T _J = 25 °C, unless otherwise noted) PARAMETER SYMBOL TEST CONDITIONS MIN. TYP. MAX. UN									
	STWIDOL	TEST CONDITIONS	IVIIIN.	ITP.	WAX.	UNIT			
Static	T		T	T	T	ı			
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	45	-	-	V			
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2	-	4				
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA			
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 45 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1	μА			
	1033	V_{DS} = 36 V, V_{GS} = 0 V, T_J = 85 °C	-	-	10				
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \geq 10~V,~V_{GS} = 10~V$	180	-	-	Α			
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	-	1.6	2.0	mΩ			
Forward Transconductance a	9 _{fs}	$V_{DS} = 5 \text{ V}, I_D = 20 \text{ A}$	-	100	-	S			
Dynamic ^b				•					
Input Capacitance	C _{iss}		-	5080	-	pF			
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 20 \text{ V}, f = 1 \text{ MHz}$	-	1310	-				
Reverse Transfer Capacitance	C _{rss}		-	9	-				
Total Gate Charge ^c	Qg		-	59		nC			
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 20 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	-	16	-				
Gate-Drain Charge ^c	Q _{gd}		-	7.3	-				
Gate Resistance	R _g	f = 1 MHz	-	6.5	-	Ω			
Turn-On Delay Time ^c	t _{d(on)}		-	20	-	ns			
Rise Time ^c	t _r	$V_{DD} = 20 \text{ V}, R_{I} = 2 \Omega$	-	10	-				
Turn-Off Delay Time c	t _{d(off)}	$I_D = 20 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 3 \Omega$	-	58	-				
Fall Time ^c	t _f		-	12	-				
Drain-Source Body Diode Ratings ar	nd Characteri	stics ^b (T _C = 25 °C)							
Continuous Source Current	Is	T _C = 25 °C	-	-	180	Α			
Pulsed Source Current	I _{SM}		-	-	720	Α			
Forward Voltage ^a	V_{SD}	I _F = 1 A, V _{GS} = 0 V	-	-	1.0	V			
Reverse Recovery Time	t _{rr}	1 00 A di/dk 100 A fra	-	28	-	ns			
Reverse Recovery Charge	Q _{rr}	$I_F = 20 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$	-	76	-	μC			

Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



5 V



180 A

A/div.

20

0 A

0 V

Drain Current

VGS = 10 V thru 8 V

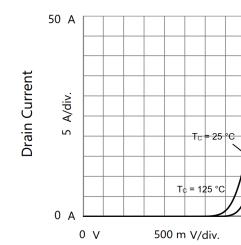
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

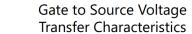
VGS = 7 V

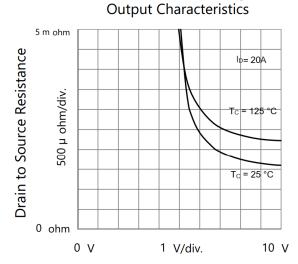
VGS = 6 V

VGS = 5 V

5 V

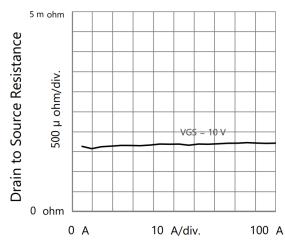




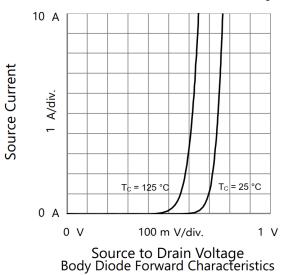


500 m V/div.

Drain to Source Voltage



Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltage



Drain to Source Resistance vs. Drain Current

10 n F

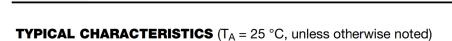
O V

5 V/div.

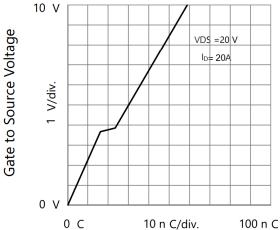
45 V

Drain Current

Drain to Source Voltage Capacitances



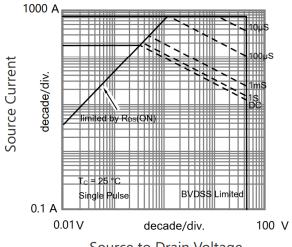
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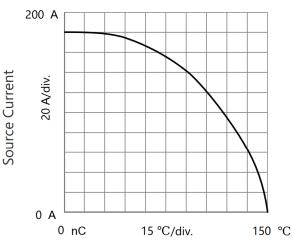
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SEMICONDUCTOR

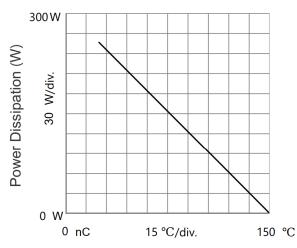
0 C 10 n C/div. **Gate Charge** Gate to Source Voltage vs. GateCharge



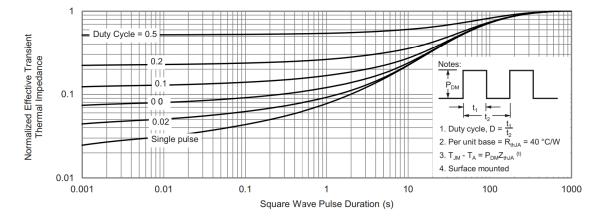
Source to Drain Voltage Safe Operating Area, Junction-to-Ambient







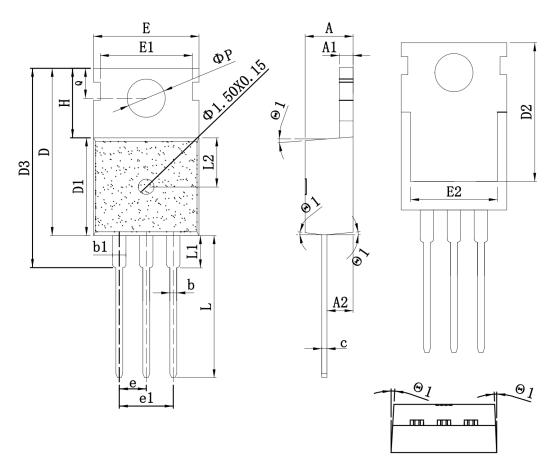
T_C - Case Temperature Power Derating



Normalized Thermal Transient Impedance, Junction-to-Ambient



TO-220_3L-A PACKAGE OUTLINE

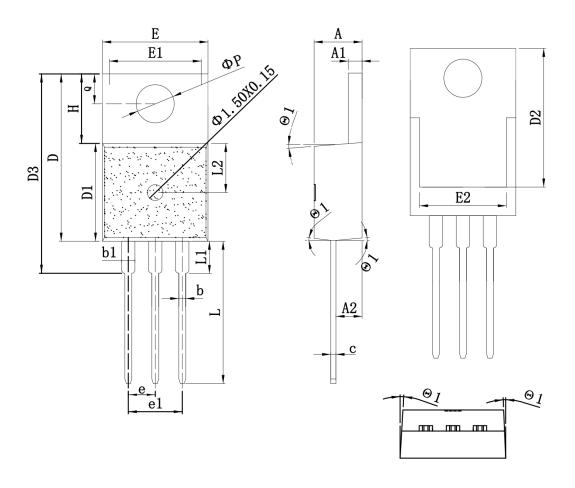


COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

SYMBOL	mm			SYMBOL	mm _		
	MIN	TYP	MAX	SIMBOL	MIN	TYP	MAX
A	4.15	4.50	4.80	E1	8.25	8.70	9.15
A1	1.15	1.30	1.50	E2	7.20	8.00	8.80
A2	2.10	2.40	2.65	e	2.38	2.54	2.74
b	0.65	0.80	1.00	e1	5.08REF		
bl	1.10	1.33	1.80	Н	6.20	6.50	6.90
С	0.35	0.50	0.65	L	12.75	13.28	13.70
D	14.25	15.75	16.15	L1	1	1	3.50
D1	8.70	9.20	9.60	L2	2.30	4.65	7.00
D2	12.30	13.10	13.85	φP	3.40	3.65	3.85
D3	16.20	18.80	20.60	Q	2.50	2.80	3.00
Е	8.68	10.02	11.00	θ	2°	1	7°



TO-220_3L-B PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

SYMBOL	mm			SYMBOL	mm		
	MIN	TYP	MAX	SIMBOL	MIN	TYP	MAX
A	4.15	4.50	4.80	E1	8.25	8.70	9.15
A1	1.15	1.30	1.50	E2	7.20	8.00	8.80
A2	2.10	2.40	2.65	e	2.38	2.54	2.74
b	0.65	0.80	1.00	e1	5.08REF		
b1	1.10	1.33	1.80	Н	6.20	6.50	6.90
c	0.35	0.50	0.65	L	12.75	13.28	13.70
D	14.25	15.75	16.15	L1	1	-	3.50
D1	8.70	9.20	9.60	L2	2.30	4.65	7.00
D2	12.30	13.10	13.85	φP	3.40	3.65	3.85
D3	16.20	18.80	20.60	Q	2.50	2.80	3.00
Е	8.68	10.02	11.00	θ	2°	-	7°





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